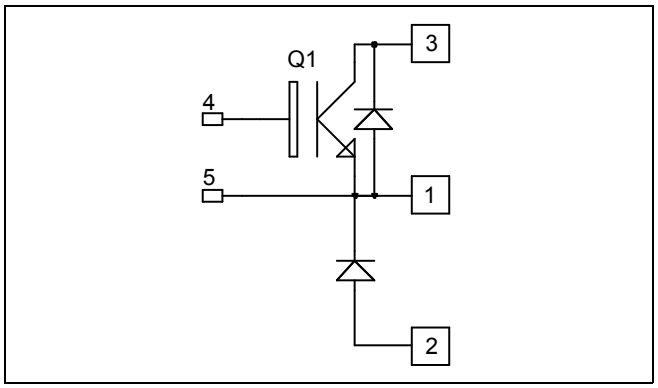
APTGF300SK120D3G

Buck Chopper NPT IGBT Power Module

V_{CES} = 1200V
I_C = 300A @ Tc = 80°C

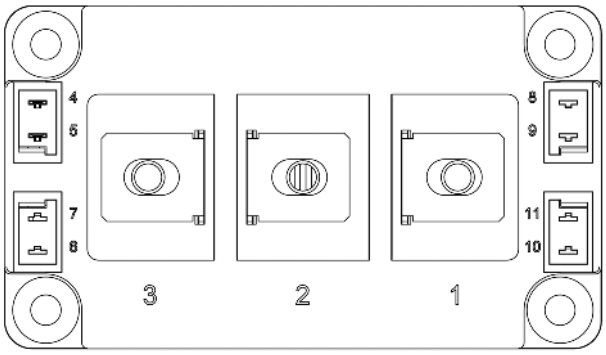


Application

- AC and DC motor control
- Switched Mode Power Supplies

Features

- Non Punch Through (NPT) FAST IGBT
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 50 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- High level of integration
- M6 power connectors



Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- RoHS Compliant

All ratings @ T_j = 25°C unless otherwise specified

Absolute maximum ratings

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{CES}	Collector - Emitter Breakdown Voltage		1200	V
I_C	Continuous Collector Current	T_C = 25°C	420	A
		T_C = 80°C	300	
I_{CM}	Pulsed Collector Current	T_C = 25°C	600	
V_{GE}	Gate – Emitter Voltage		±20	V
P_D	Maximum Power Dissipation	T_C = 25°C	2100	W
RBSOA	Reverse Bias Safe Operating Area	T_j = 125°C	600A@1150V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	V_{GE} = 0V, V_{CE} = 1200V				150	µA
$V_{CE(on)}$	Collector Emitter on Voltage	V_{GE} = 15V I_C = 300A	T_j = 25°C		3.2	3.7	V
			T_j = 125°C		3.9		
$V_{GE(th)}$	Gate Threshold Voltage	V_{GE} = V_{CE} , I_C = 12 mA		5.2	5.8	6.4	V
I_{GES}	Gate – Emitter Leakage Current	V_{GE} = 20V, V_{CE} = 0V				1.2	µA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
C_{ies}	Input Capacitance	V_{GE} = 0V, V_{CE} = 25V f = 1MHz			19		nF
C_{res}	Reverse Transfer Capacitance				1.4		
Q_G	Gate charge	V_{GE}=±15V, I_C = 300A V_{CE} = 600V			3		µC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) V_{GE} = ±15V V_{Bus} = 600V I_C = 200A R_G = 3.3Ω			100		ns
T_r	Rise Time				60		
$T_{d(off)}$	Turn-off Delay Time				530		
T_f	Fall Time				30		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) V_{GE} = ±15V V_{Bus} = 600V I_C = 200A R_G = 3.3Ω			110		ns
T_r	Rise Time				70		
$T_{d(off)}$	Turn-off Delay Time				550		
T_f	Fall Time				40		
E_{on}	Turn On Energy	V_{GE} = ±15V V_{Bus} = 600V I_C = 300A R_G = 3.3Ω	T_j = 125°C		25		mJ
E_{off}	Turn Off Energy		T_j = 125°C		21		
I_{sc}	Short Circuit data	V_{GE} ≤15V ; V_{Bus} = 900V t_p ≤ 10µs ; T_j = 125°C			2000		A
R_{thJC}	Junction to Case Thermal Resistance					0.06	°C/W

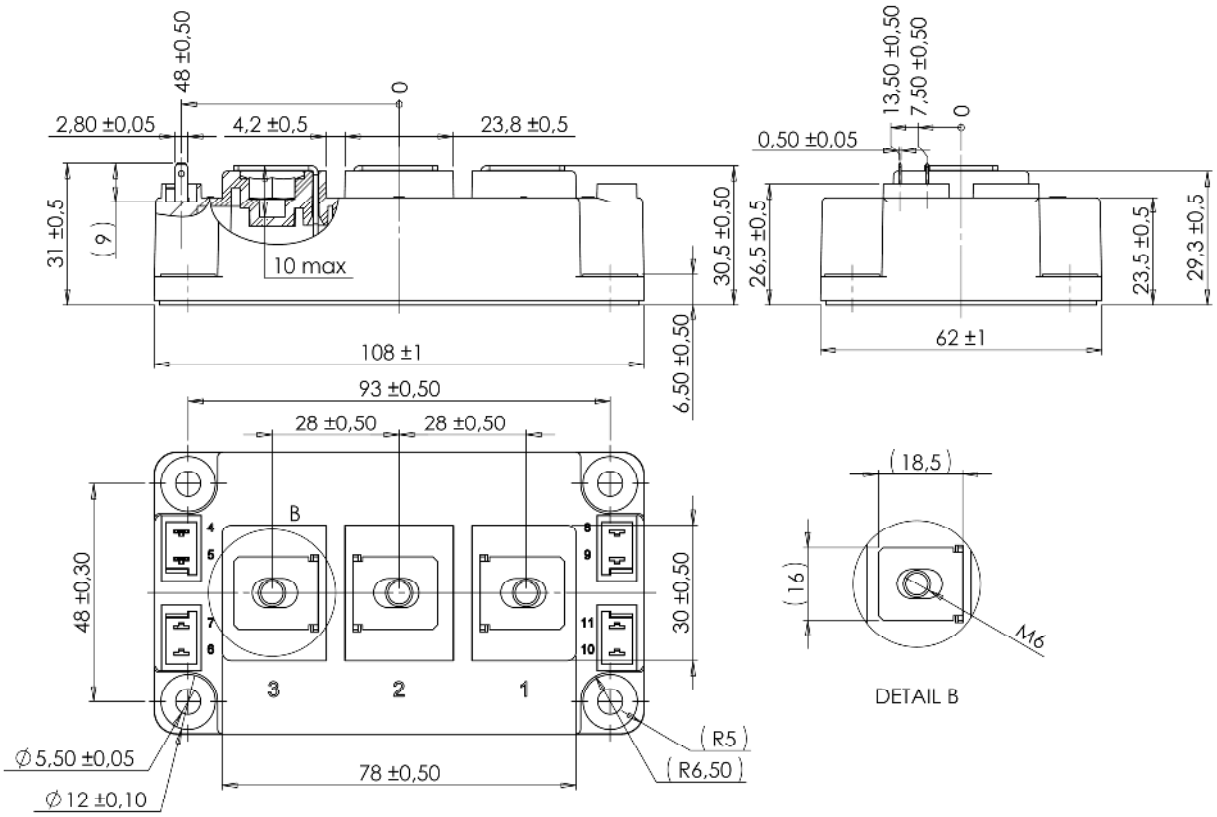
Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I_{RRM}	Maximum Reverse Leakage Current	V_R = 1200V				250	µA
I_F	DC Forward Current		Tc = 80°C		300		A
V_F	Diode Forward Voltage	I_F = 300A	T_j = 25°C		2.1		V
			T_j = 125°C		1.9		
t_{rr}	Reverse Recovery Time	I_F = 300A V_R = 600V di/dt =4500A/µs	T_j = 25°C		120		ns
			T_j = 125°C		210		
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		19		µC
			T_j = 125°C		53		
E_{rr}	Reverse Recovery Energy		T_j = 25°C		7		mJ
			T_j = 125°C		15		
R_{thJC}	Junction to Case Thermal Resistance					0.12	°C/W

Thermal and package characteristics

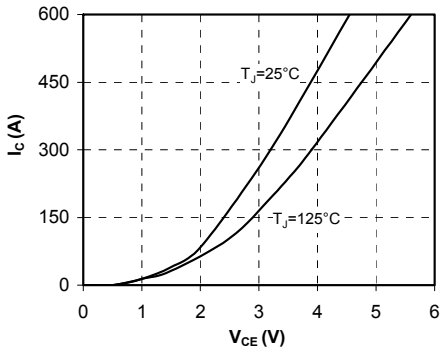
Symbol	*Characteristic*			*Min*	*Max*	*Unit*
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000		V
T_J	Operating junction temperature range			-40	150	°C
T_{STG}	Storage Temperature Range			-40	125	
T_{JOP}	Recommended junction temperature under switching conditions			-40	$T_J$max - 25	
T_C	Operating Case Temperature			-40	125	
Torque	Mounting torque	For terminals	M6	3	5	N.m
		To Heatsink	M6	3	5	
Wt	Package Weight				350	g

D3 Package outline (dimensions in mm)

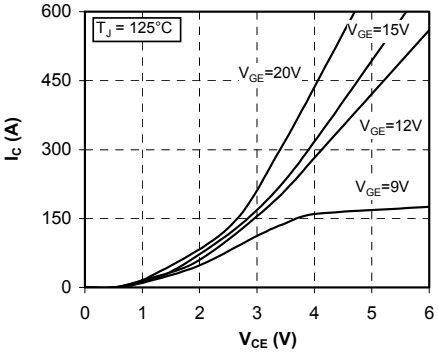


Typical Performance Curve

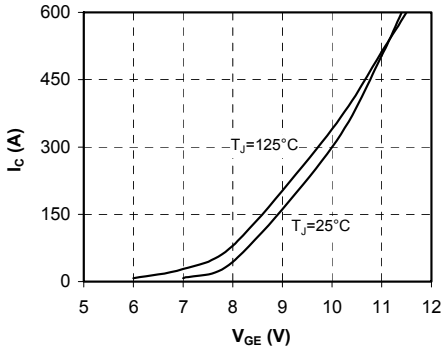
Output Characteristics (V_{GE}=15V)



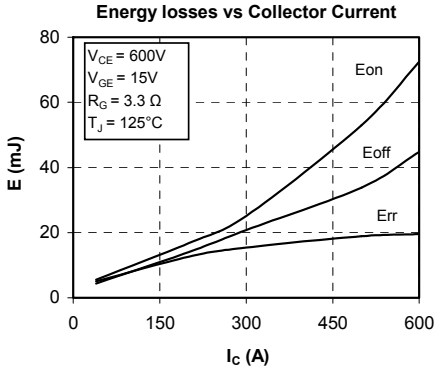
Output Characteristics



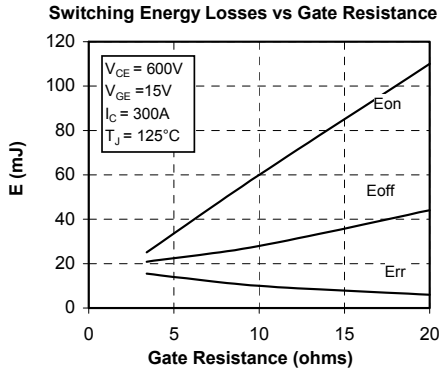
Transfert Characteristics



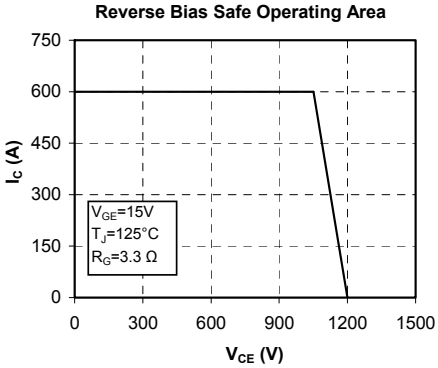
Energy losses vs Collector Current



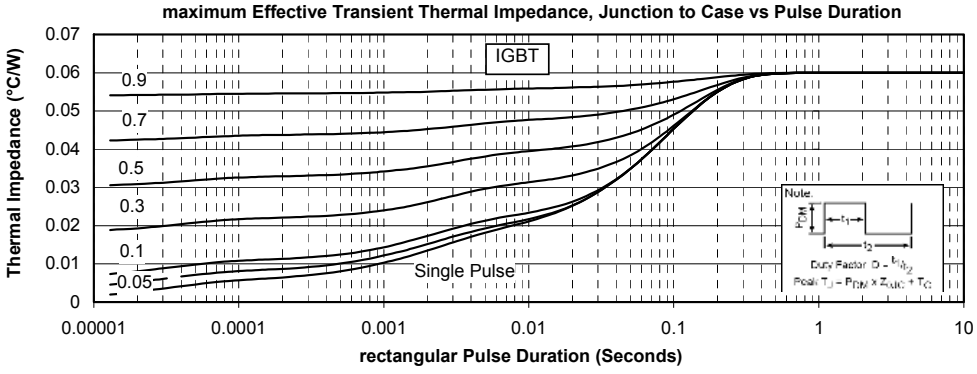
Switching Energy Losses vs Gate Resistance



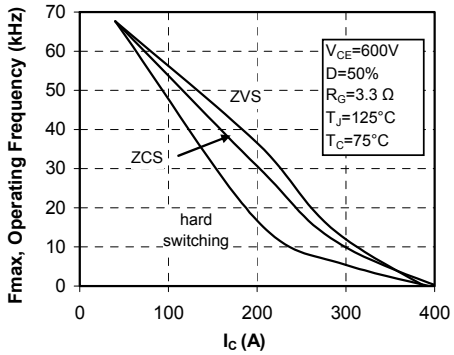
Reverse Bias Safe Operating Area



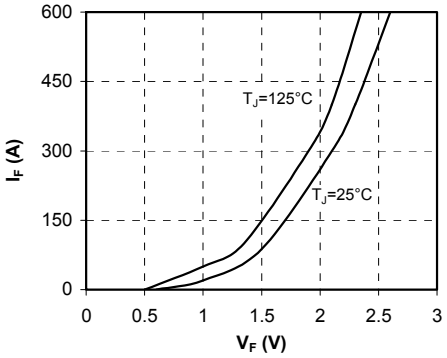
maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration



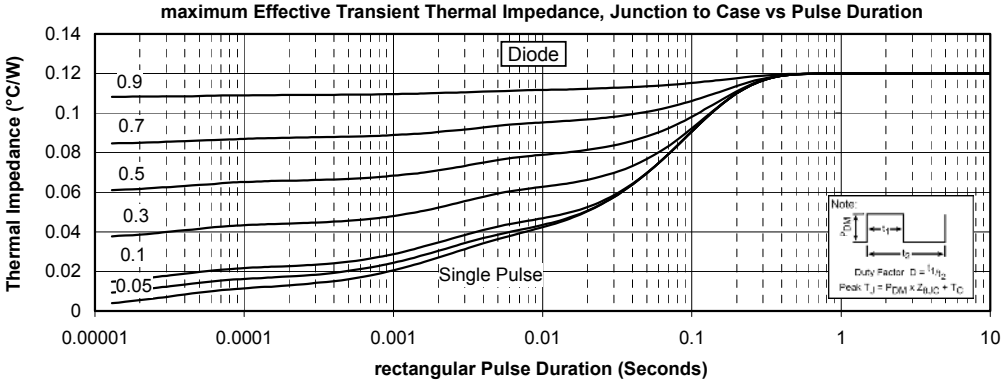
Operating Frequency vs Collector Current



Forward Characteristic of diode



maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration



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